



3-29-06

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Fu-Hsin Chen, et al.	§	Docket No.:	24061.79 / 2003-0322
Serial No.:	10/801,234	§	Examiner:	Thomas L. Dickey
Filed:	March 16, 2004	§	Art Unit:	2811
For:	High-Voltage MOS Transistor and Method for Fabricating the Same	§	Conf. No.:	2028

TRANSMITTAL

Mail Stop: Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450


Dear Sir:

Enclosed for filing in the above-identified patent application.

1. Notice of Appeal;
2. Petition for Three-Month Extension of Time;
3. Pre-Appeal Brief Request for Review; and
4. Return postcard.

The Director is authorized to charge any deficiency fees or credit any overpayments associated with this communication to Deposit Account No. 08-1394 of Haynes and Boone, LLP.

Respectfully submitted,


David M. O'Dell
Registration No. 42,044

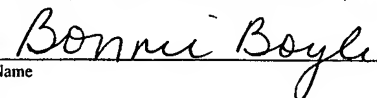
Date: March 28, 2006

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File: 24061.79

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as Express Mail Service, Label No. EV369677911US in an envelope addressed to: Commissioner For Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the date March 28, 2006.


Name